

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub>           | I <sub>D</sub><br>T <sub>C</sub> = +25°C |
|-------------------|-------------------------------|------------------------------------------|
| 60V               | 1.6mΩ @ V <sub>GS</sub> = 10V | 215A                                     |

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

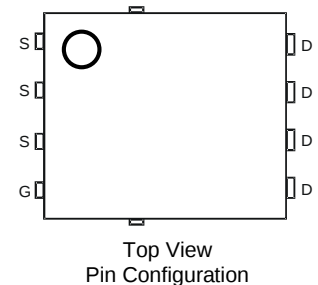
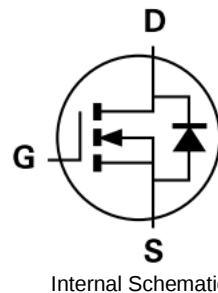
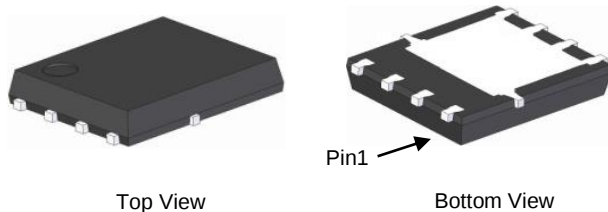
## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMTH61M8SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (Type K)

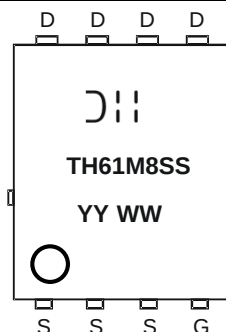


## Ordering Information (Note 4)

| Part Number     | Case                   | Packaging           |
|-----------------|------------------------|---------------------|
| DMTH61M8SPSQ-13 | PowerDI5060-8 (Type K) | 2,500 / Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



PowerDI5060-8 (Type K)

⌋⌋⌋ = Manufacturer's Marking  
TH61M8SS = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Year (ex: 20 = 2020)  
WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                                  | Symbol           | Value      | Unit |
|-----------------------------------------------------------------|------------------|------------|------|
| Drain-Source Voltage                                            | V <sub>DSS</sub> | 60         | V    |
| Gate-Source Voltage                                             | V <sub>GSS</sub> | ±20        | V    |
| Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)        | I <sub>D</sub>   | 215<br>150 | A    |
| Maximum Continuous Body Diode Forward Current (Note 6)          | I <sub>S</sub>   | 215        | A    |
| Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)              | I <sub>DM</sub>  | 860        | A    |
| Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%) | I <sub>SM</sub>  | 860        | A    |
| Avalanche Current, L = 1mH                                      | I <sub>AS</sub>  | 35.8       | A    |
| Avalanche Energy, L = 1mH                                       | E <sub>AS</sub>  | 640.8      | mJ   |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value       | Unit |
|--------------------------------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | P <sub>D</sub>                    | 3.2         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | 47          | °C/W |
| Total Power Dissipation (Note 6)                 | P <sub>D</sub>                    | 167         | W    |
| Thermal Resistance, Junction to Case (Note 6)    | R <sub>θJC</sub>                  | 0.9         | °C/W |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +175 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol              | Min | Typ   | Max  | Unit | Test Condition                                                                          |
|-----------------------------------------|---------------------|-----|-------|------|------|-----------------------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 7)</b>     |                     |     |       |      |      |                                                                                         |
| Drain-Source Breakdown Voltage          | BV <sub>DSS</sub>   | 60  | —     | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                                            |
| Zero Gate Voltage Drain Current         | I <sub>DSS</sub>    | —   | —     | 1    | μA   | V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V                                             |
| Gate-Source Leakage                     | I <sub>GSS</sub>    | —   | —     | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                                            |
| <b>ON CHARACTERISTICS (Note 7)</b>      |                     |     |       |      |      |                                                                                         |
| Gate Threshold Voltage                  | V <sub>GS(TH)</sub> | 2   | —     | 4    | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                              |
| Static Drain-Source On-Resistance       | R <sub>DS(ON)</sub> | —   | 1.1   | 1.6  | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A                                             |
| Diode Forward Voltage                   | V <sub>SD</sub>     | —   | 0.7   | 1.2  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A                                              |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b> |                     |     |       |      |      |                                                                                         |
| Input Capacitance                       | C <sub>iss</sub>    | —   | 8306  | —    | pF   | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz                                   |
| Output Capacitance                      | C <sub>oss</sub>    | —   | 2735  | —    |      |                                                                                         |
| Reverse Transfer Capacitance            | C <sub>rss</sub>    | —   | 184   | —    |      |                                                                                         |
| Gate Resistance                         | R <sub>g</sub>      | —   | 3.0   | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz                                    |
| Total Gate Charge                       | Q <sub>g</sub>      | —   | 130.6 | —    | nC   | V <sub>DS</sub> = 30V, I <sub>D</sub> = 30A, V <sub>GS</sub> = 10V                      |
| Gate-Source Charge                      | Q <sub>gs</sub>     | —   | 30.4  | —    |      |                                                                                         |
| Gate-Drain Charge                       | Q <sub>gd</sub>     | —   | 28.1  | —    |      |                                                                                         |
| Turn-On Delay Time                      | t <sub>D(ON)</sub>  | —   | 11.3  | —    | ns   | V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A, R <sub>g</sub> = 3Ω |
| Turn-On Rise Time                       | t <sub>r</sub>      | —   | 28.5  | —    |      |                                                                                         |
| Turn-Off Delay Time                     | t <sub>D(OFF)</sub> | —   | 86.2  | —    |      |                                                                                         |
| Turn-Off Fall Time                      | t <sub>f</sub>      | —   | 47.6  | —    |      |                                                                                         |
| Body Diode Reverse Recovery Time        | t <sub>RR</sub>     | —   | 70.4  | —    | ns   | I <sub>F</sub> = 30A, di/dt = 100A/μs                                                   |
| Body Diode Reverse Recovery Charge      | Q <sub>RR</sub>     | —   | 127   | —    | nC   |                                                                                         |

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  6. Thermal resistance from junction to soldering point (on the exposed drain pad).
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

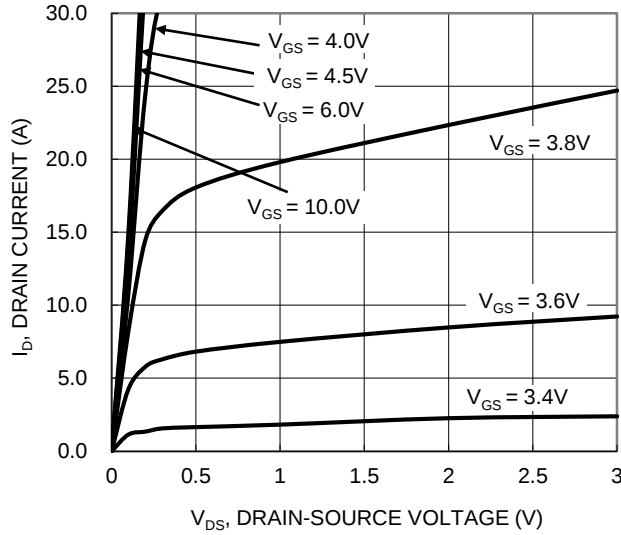


Figure 1. Typical Output Characteristic

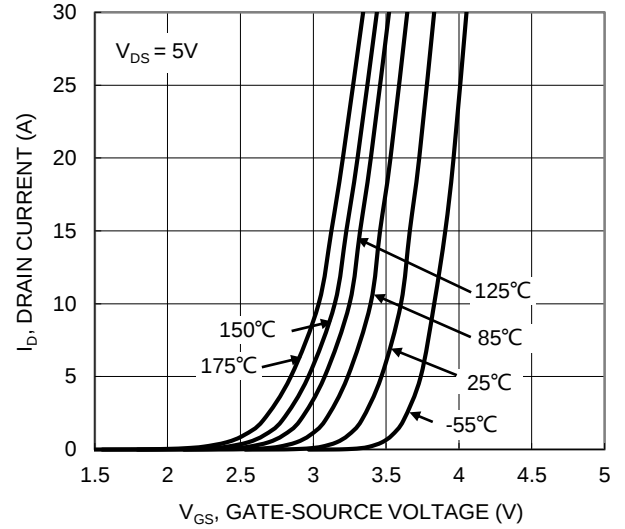


Figure 2. Typical Transfer Characteristic

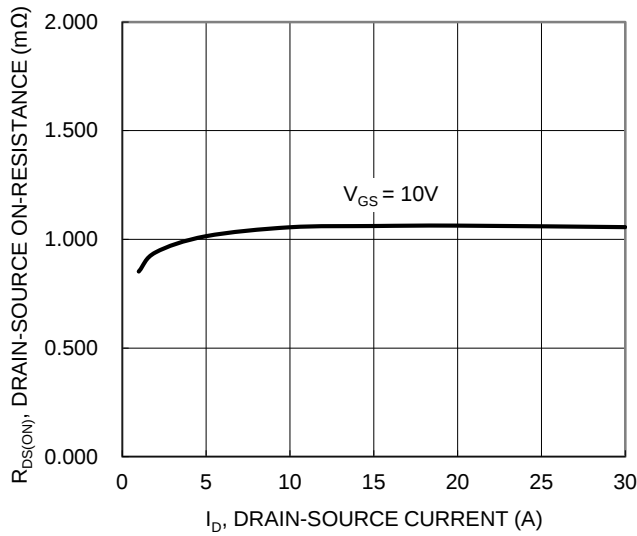


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

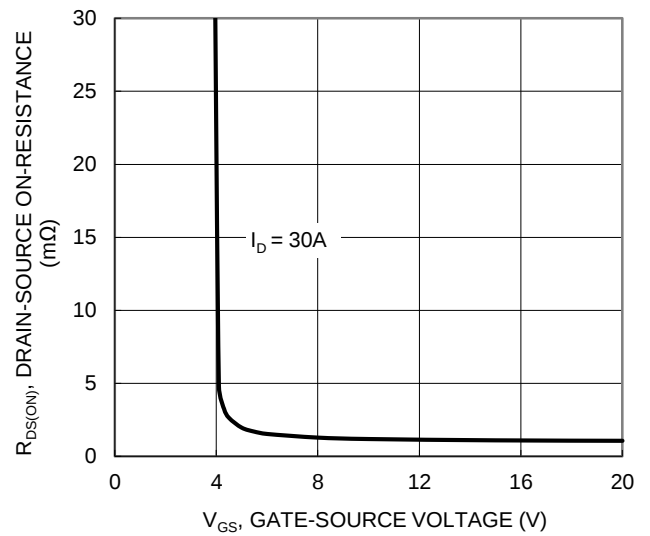


Figure 4. Typical Transfer Characteristic

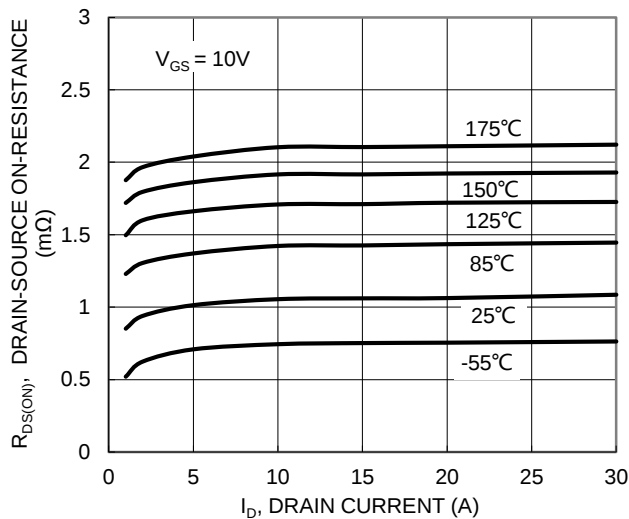


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

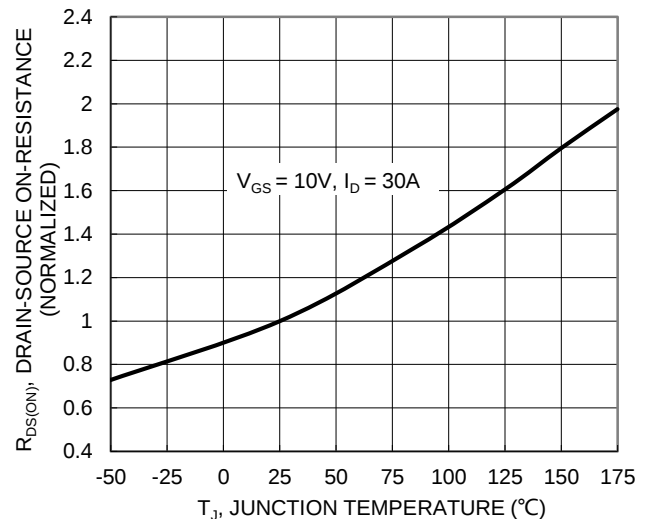
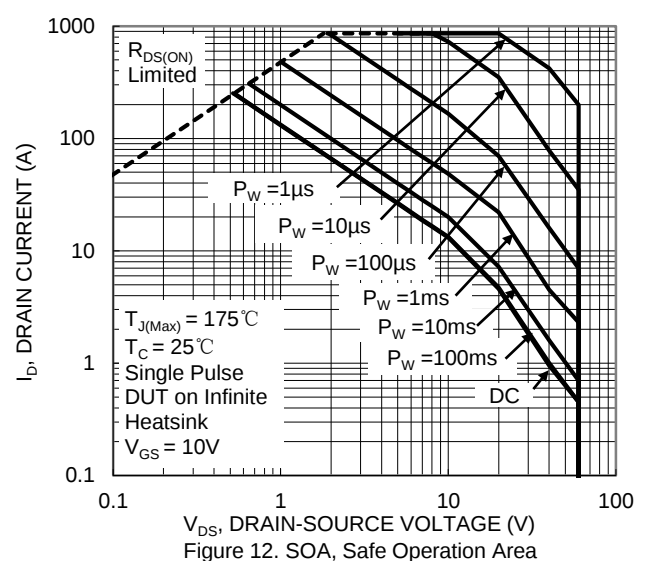
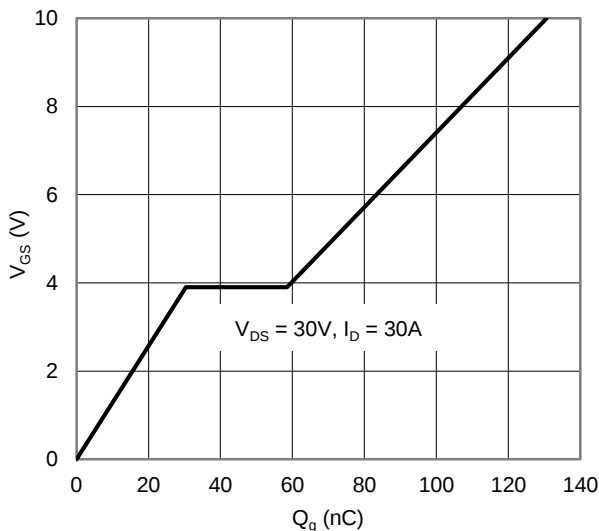
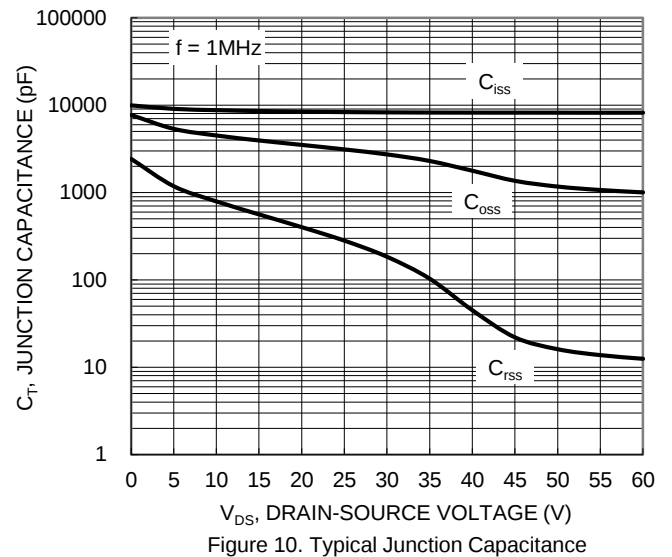
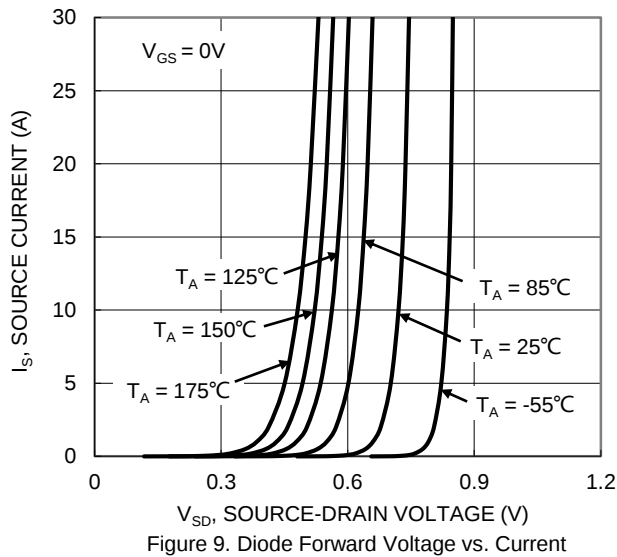
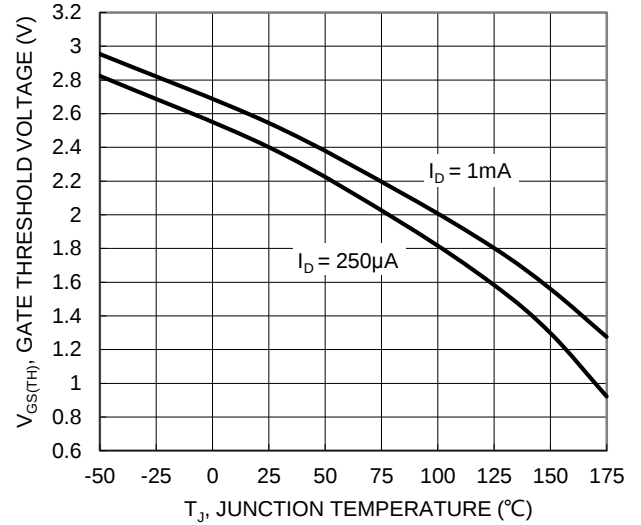
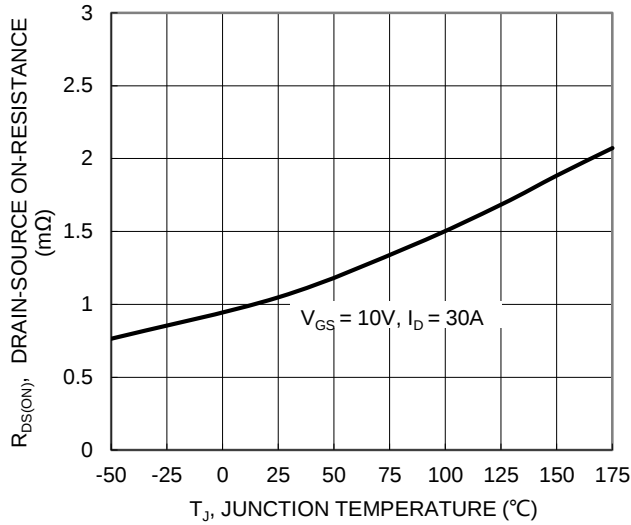


Figure 6. On-Resistance Variation with Temperature



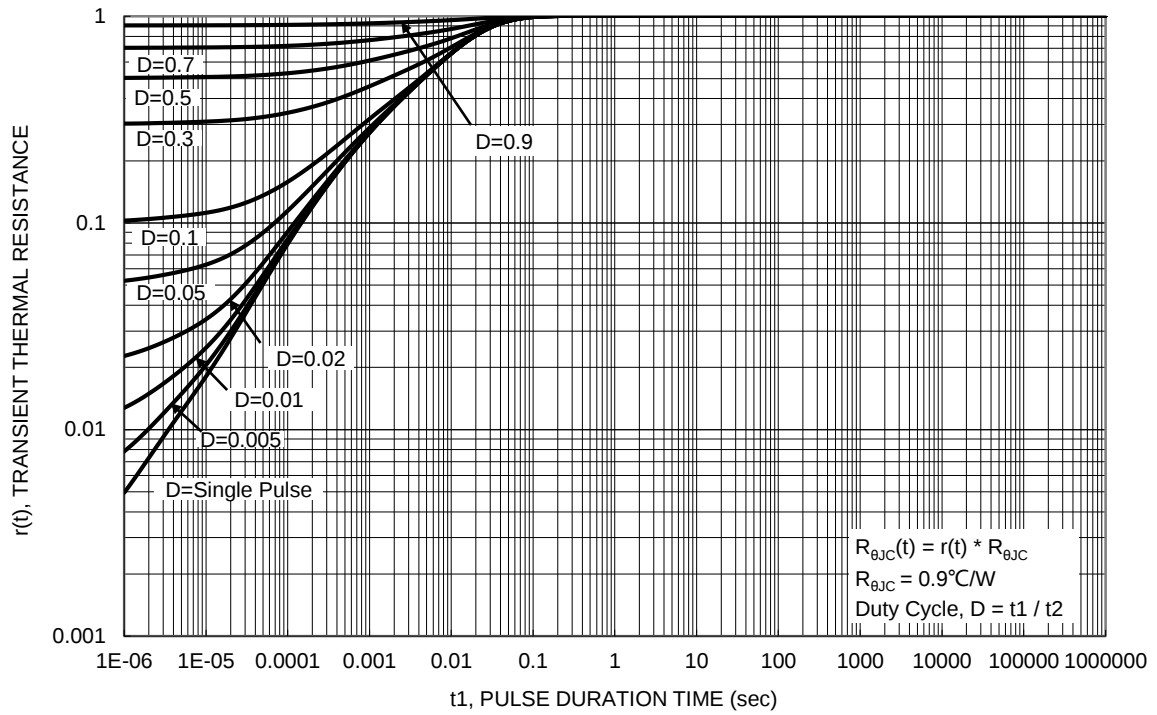
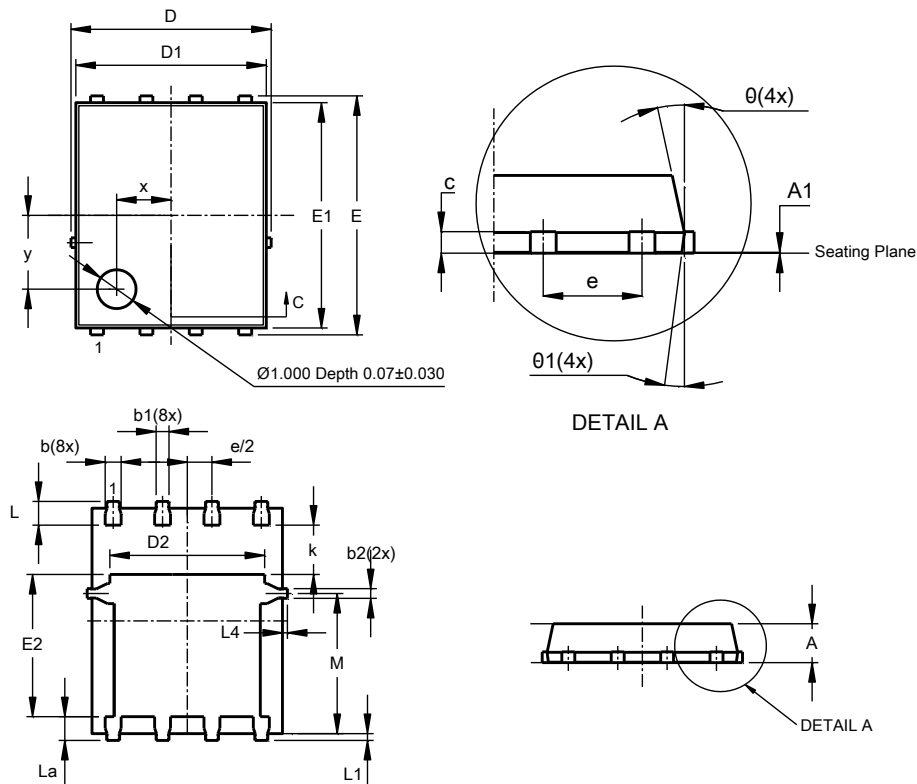


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### PowerDI5060-8 (Type K)

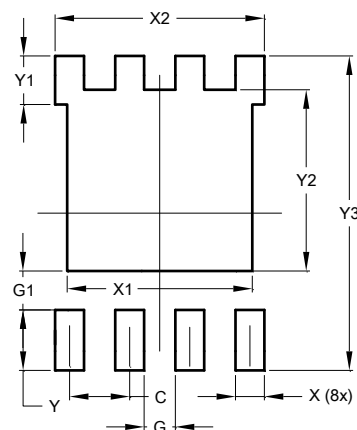


| PowerDI5060-8<br>(Type K) |          |       |       |
|---------------------------|----------|-------|-------|
| Dim                       | Min      | Max   | Typ   |
| A                         | 0.90     | 1.10  | 1.00  |
| A1                        | 0        | 0.05  | 0.02  |
| b                         | 0.33     | 0.51  | 0.41  |
| b1                        | 0.300    | 0.366 | 0.333 |
| b2                        | 0.20     | 0.35  | 0.25  |
| c                         | 0.23     | 0.33  | 0.277 |
| D                         | 5.15 BSC |       |       |
| D1                        | 4.85     | 4.95  | 4.90  |
| D2                        | -        | -     | 3.98  |
| E                         | 6.15 BSC |       |       |
| E1                        | 5.75     | 5.85  | 5.80  |
| E2                        | 3.56     | 3.725 | 3.66  |
| e                         | 1.27 BSC |       |       |
| k                         | -        | -     | 1.27  |
| L                         | 0.51     | 0.71  | 0.61  |
| La                        | 0.51     | 0.675 | 0.61  |
| L1                        | 0.05     | 0.20  | 0.175 |
| L4                        | -        | -     | 0.125 |
| M                         | 3.50     | 3.71  | 3.605 |
| x                         | -        | -     | 1.400 |
| y                         | -        | -     | 1.900 |
| θ                         | 10°      | 12°   | 11°   |
| θ1                        | 6°       | 8°    | 7°    |
| All Dimensions in mm      |          |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### PowerDI5060-8 (Type K)



| Dimensions | Value<br>(in mm) |
|------------|------------------|
| C          | 1.270            |
| G          | 0.660            |
| G1         | 0.820            |
| X          | 0.610            |
| X1         | 3.910            |
| X2         | 4.420            |
| Y          | 1.270            |
| Y1         | 1.020            |
| Y2         | 3.810            |
| Y3         | 6.610            |

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